

Attorney Docket No. 0756-2131

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:

Shunpei YAMAZAKI et al.

Serial No. 09/535,015

Filed: March 24, 2000

For: METHOD OF MANUFACTURING A  
SEMICONDUCTOR DEVICE

) Group Art Unit: 2811

) Examiner: S. Crane

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Honorable Commissioner of Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, Applicant submits herewith a Form PTO-1449 listing information known to Applicant and requests that this information be made of record in the above identified application. Copies are submitted herewith in accordance with 37 C.F.R. 1.98(a).

A check in the amount of \$180 is being submitted to comply with the provisions of 37 C.F.R. § 1.97(c).

Respectfully submitted,

Eric J. Robinson  
Reg. No. 38,285

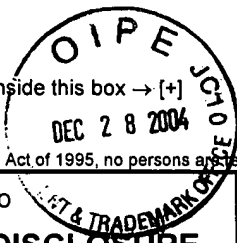
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# **INFORMATION DISCLOSURE STATEMENT BY APPLICANT**

(use as many sheets as necessary)

## **Complete if Known**

Application Number	09/535,015
Filing Date	March 24, 2000
First Named Inventor	Shunpei YAMAZAKI et al.
Group Art Unit	2811
Examiner Name	S. Crane
Attorney Docket Number	0756-2131

Sheet 1 of 1

## **U.S. PATENT DOCUMENTS**

Examiner Initials	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
		5,531,862		Otsubo et al.	07/02/1996	
		5,575,883		Nishikawa	11/19/1996	
		5,704,986		Chen et al.	01/06/1998	
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		6,162,704		Yamazaki et al.	12/19/2000	
		6,177,302		Yamazaki et al.	01/23/2001	
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		6,620,711		Yamazaki	09/16/2003	

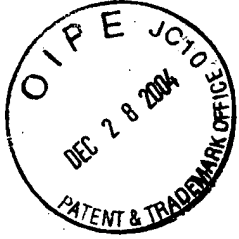
## **FOREIGN PATENT DOCUMENTS**

Examiner Initials	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>5</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
		JP	08-045839			02/16/1996		Abst.
		JP	08-045840			02/16/1996		Abst.
		JP	08-097169			04/12/1996		Abst.

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This will acknowledge receipt of the following:

1. Information Disclosure Statement with Certificate of Mailing
2. Form PTO-1449

in re PATENT application of:

Shunpei YAMAZAKI et al.

Serial No. 09/535,015

Filed: 03/24/2000

Title: METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE

Due date: 09/15/2000

0756-2131

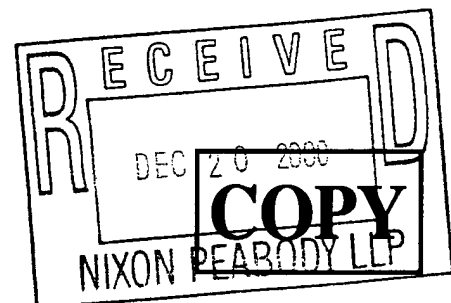
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT application of: )  
 Shunpei YAMAZAKI et al. ) Art Unit: 2825  
 Serial No. 09/535,015 ) Examiner: Unassigned  
 Filed: 03/24/2000 )  
 For: METHOD OF MANUFACTURING A )  
 SEMICONDUCTOR DEVICE )

### INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents  
 Washington, D.C. 20231

Sir:

In accordance with the provisions of 37 C.F.R. 1.56 and 37 C.F.R. 1.97-1.99, it is requested that the reference(s) listed on the attached Form PTO-1449 be made of record in the above-identified application. Copies of the references are submitted herewith in accordance with 37 C.F.R. 1.98(a).

The following two articles were cited by the Examiner in the following Applications:

*Kuo, "Thin Film Transistor Technologies", Vol. 94-35, PP. 116-122, The Electrochemical Society Proceedings, cited in Serial No's 08/784,292 and 09/233,450.*

*"Thermo Auto-Chrome Full Color Recording Technology", May 31, 1995, Technology Information Association, Patent No. 6,093,934, Serial No. 08/785,536.*

The Commissioner is hereby authorized to charge fees under 37 C.F.R. §§1.16, 1.17, 1.20(a), 1.20(b), 1.20(c), and 1.20(d) (except the Issue Fee) which may be required now or hereafter, or credit any overpayment to Deposit Account No. 19-2380. A duplicate copy of this sheet is attached.

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Eric J. Robinson  
Reg. No. 38,285

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8180 Greensboro Drive, Suite 800  
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Serial No. 09/535,015

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Filing Date: March 24, 2000

Group Art Unit: 2825

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	5,619,044	04/08/1997	Makita et al.			
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Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date (if appropriate)
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	6,048,758	04/11/2000	Yamazaki et al.			
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Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
	0 178 447	10/09/1984	EP			Engl.	
	01-187814	07/27/1989	Japan			Full	
	01-187874	07/27/1989	Japan			Abst.	
	01-187875	07/27/1989	Japan			Abst.	
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	02-148687	06/07/1990	Japan			Abst.	
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	05-107561	04/30/1993	Japan			Abst.	
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						Yes	No
	08-129360	05/21/1996	Japan			Abst.	
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	08-241057	09/17/1996	Japan			Abst.	
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	60-105216	06/10/1985	Japan			Full	
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